

### Short circuit rugged 1200 V TRENCHSTOP™ IGBT 7 technology

#### Features

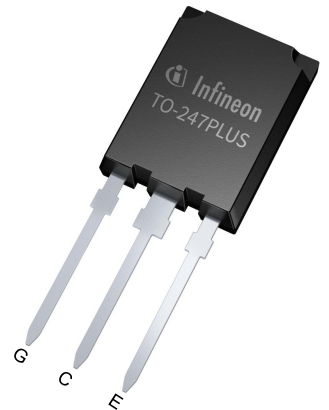
- $V_{CE} = 1200\text{ V}$
- $I_C = 75\text{ A}$
- Low saturation voltage  $V_{CEsat} = 2.0\text{ V}$  at  $T_{vj} = 175^\circ\text{C}$
- Short circuit ruggedness  $8\ \mu\text{s}$
- Wide range of  $dv/dt$  controllability
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

#### Potential applications

- Industrial power supplies
- Solar

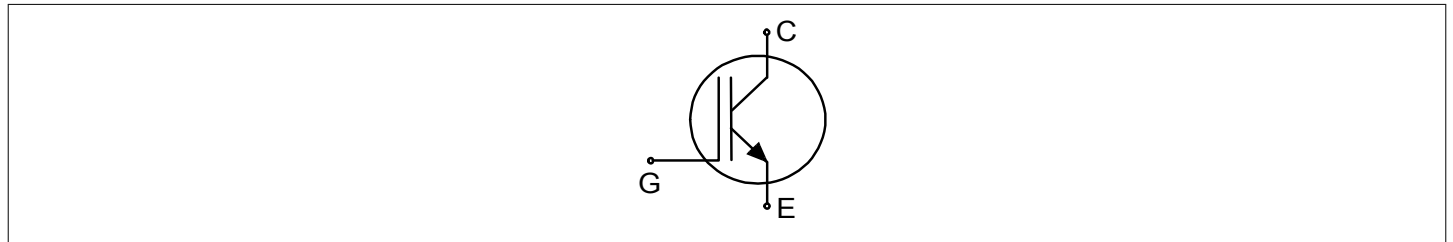
#### Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



- Halogen-free
- Lead-free
- Green
- RoHS

#### Description



Type	Package	Marking
IGQ75N120S7	PG-TO247-3-PLUS-NN3.7	G75MS7

## Table of contents

	<b>Description</b> .....	1
	<b>Features</b> .....	1
	<b>Potential applications</b> .....	1
	<b>Product validation</b> .....	1
	<b>Table of contents</b> .....	2
<b>1</b>	<b>Package</b> .....	3
<b>2</b>	<b>IGBT</b> .....	3
<b>3</b>	<b>Characteristics diagrams</b> .....	6
<b>4</b>	<b>Package outlines</b> .....	11
<b>5</b>	<b>Testing conditions</b> .....	12
	<b>Revision history</b> .....	13
	<b>Disclaimer</b> .....	14

## 1 Package

**Table 1** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	$L_E$			13		nH
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature	$T_{sold}$	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.17	0.24	K/W

## 2 IGBT

**Table 2** Maximum rated values

Parameter	Symbol	Note or test condition	Values		Unit
			Min.	Max.	
Collector-emitter voltage	$V_{CE}$	$T_{vj} \geq 25\text{ °C}$	1200		V
DC collector current, limited by $T_{vjmax}$	$I_C$	limited by bondwire	$T_c = 25\text{ °C}$	154	A
			$T_c = 100\text{ °C}$	103	
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpulse}$		225		A
Turn-off safe operating area		$V_{CE} \leq 1200\text{ V}, T_{vj} \leq 175\text{ °C}$	225		A
Gate-emitter voltage	$V_{GE}$		$\pm 20$		V
Transient gate-emitter voltage	$V_{GE}$	$t_p \leq 0.5\text{ }\mu\text{s}, D < 0.001$	$\pm 25$		V
Short-circuit withstand time	$t_{SC}$	$V_{CC} \leq 600\text{ V}, V_{GE} = 15\text{ V}$ , Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}, T_{vj} = 150\text{ °C}$	8		$\mu\text{s}$
Power dissipation	$P_{tot}$	$T_{vj} \leq 175\text{ °C}$	$T_c = 25\text{ °C}$	630	W
			$T_c = 100\text{ °C}$	315	

**Table 3** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.65	2	V
			$T_{vj} = 175\text{ °C}$	2		

(table continues...)

**Table 3 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Gate-emitter threshold voltage	$V_{GEth}$	$I_C = 1.5 \text{ mA}, V_{CE} = V_{GE}$	5.1	5.7	6.5	V
Zero gate-voltage collector current	$I_{CES}$	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		20	$\mu\text{A}$
			$T_{vj} = 175 \text{ }^\circ\text{C}$		6600	
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$			100	nA
Transconductance	$g_{fs}$	$I_C = 75 \text{ A}, V_{CE} = 20 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$		30		S
Short-circuit collector current	$I_{SC}$	$V_{CC} \leq 600 \text{ V}, V_{GE} = 15 \text{ V}, t_{SC} \leq 8 \text{ } \mu\text{s}$ , Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0 \text{ s}, T_{vj} = 150 \text{ }^\circ\text{C}$		450		A
Input capacitance	$C_{ies}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$		11.2		nF
Output capacitance	$C_{oes}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$		210		pF
Reverse transfer capacitance	$C_{res}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$		50		pF
Gate charge	$Q_G$	$I_C = 75 \text{ A}, V_{GE} = 15 \text{ V}, V_{CC} = 960 \text{ V}$		450		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{G(on)} = 2.1 \text{ } \Omega, R_{G(off)} = 2.1 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$	38		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		36	
Rise time (inductive load)	$t_r$	$V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{G(on)} = 2.1 \text{ } \Omega, R_{G(off)} = 2.1 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$	23		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		26	
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{G(on)} = 2.1 \text{ } \Omega, R_{G(off)} = 2.1 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$	190		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		253	
Fall time (inductive load)	$t_f$	$V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{G(on)} = 2.1 \text{ } \Omega, R_{G(off)} = 2.1 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$	107		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		230	
Turn-on energy	$E_{on}$	$V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{G(on)} = 2.1 \text{ } \Omega, R_{G(off)} = 2.1 \text{ } \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$	5.13		mJ
			$T_{vj} = 175 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		7.32	

(table continues...)

**Table 3 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Turn-off energy	$E_{off}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 2.1\ \Omega,$ $R_{G(off)} = 2.1\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		3.48		mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		6.48		
Total switching energy	$E_{ts}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 2.1\ \Omega,$ $R_{G(off)} = 2.1\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		8.6		mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		13.8		
Operating junction temperature	$T_{vj}$		-40		175	$^\circ\text{C}$	

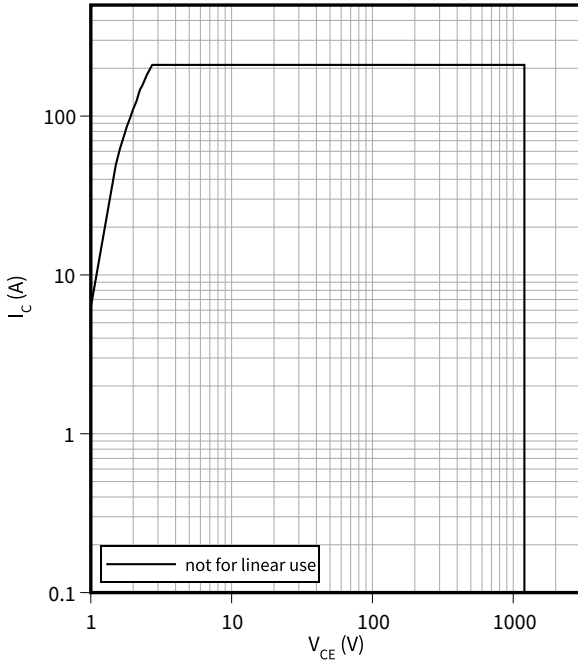
*Note: Electrical Characteristic, at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified.  
 For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.  
 Dynamic test circuit, parasitic inductance  $L_\sigma = 30\text{ nH}$ ,  $C_\sigma = 18\text{ pF}$ . Energy losses include “tail” and diode (IKQ75N120CS7) reverse recovery*

### 3 Characteristics diagrams

**Reverse bias safe operating area**

$I_C = f(V_{CE})$

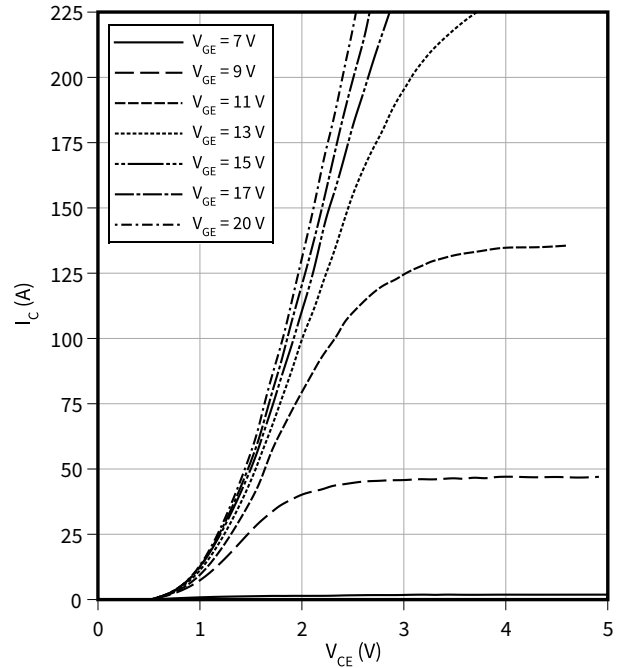
$T_{vj} \leq 175^\circ\text{C}, V_{CE} = 25\text{ V}$



**Typical output characteristic**

$I_C = f(V_{CE})$

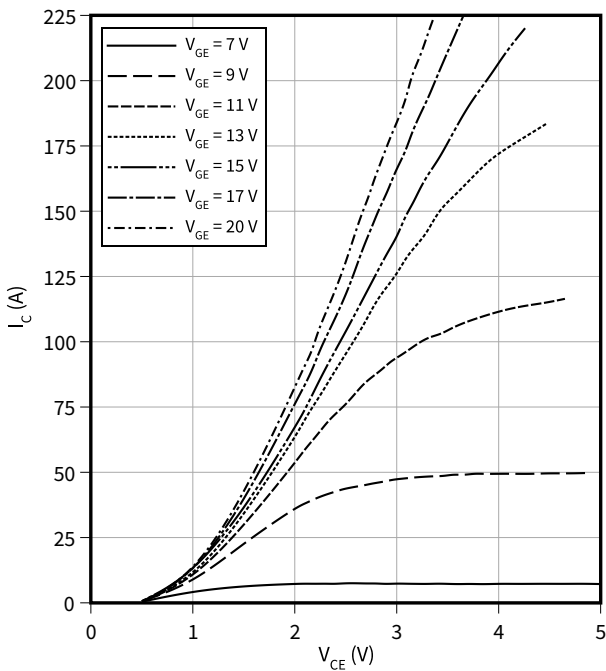
$T_{vj} = 25^\circ\text{C}$



**Typical output characteristic**

$I_C = f(V_{CE})$

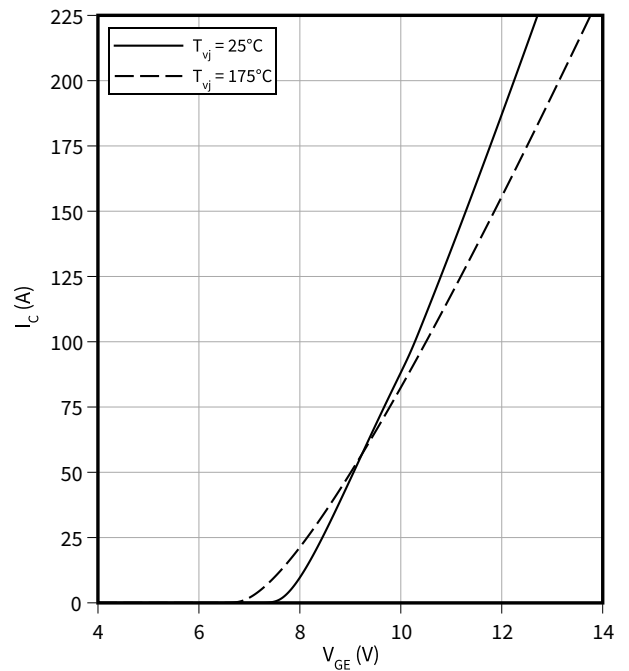
$T_{vj} = 175^\circ\text{C}$



**Typical transfer characteristic**

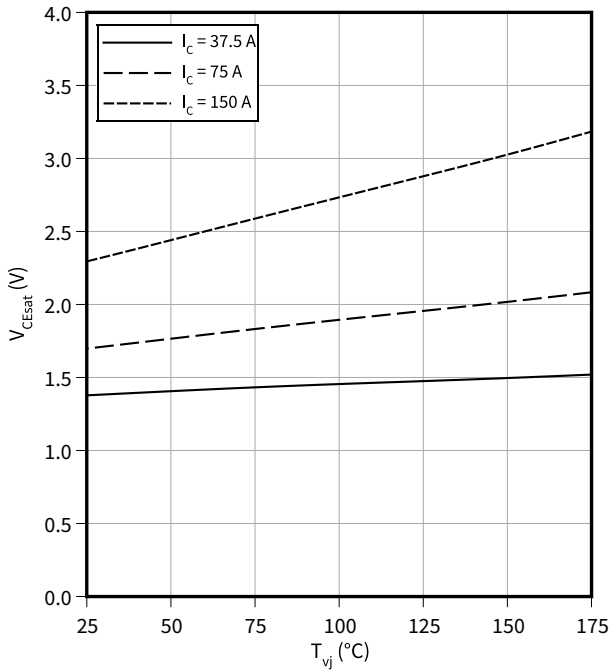
$I_C = f(V_{GE})$

$V_{CE} = 20\text{ V}$



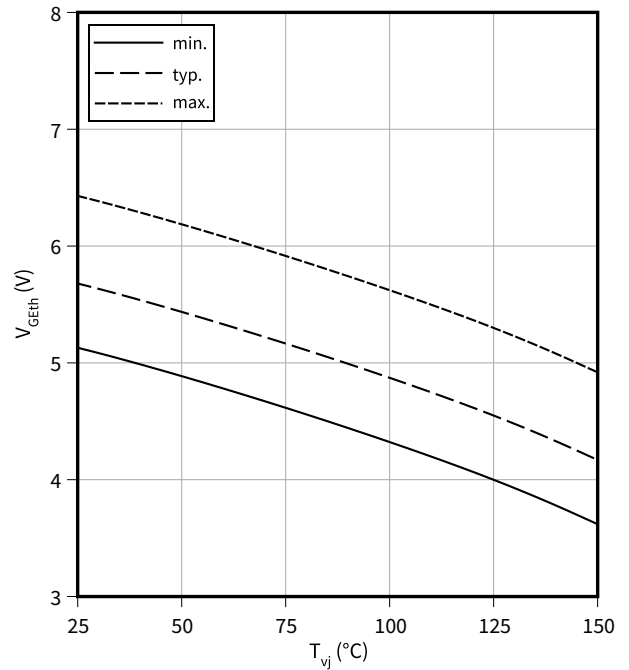
**Typical collector-emitter saturation voltage as a function of junction temperature**

$V_{CEsat} = f(T_{vj})$   
 $V_{GE} = 15 \text{ V}$



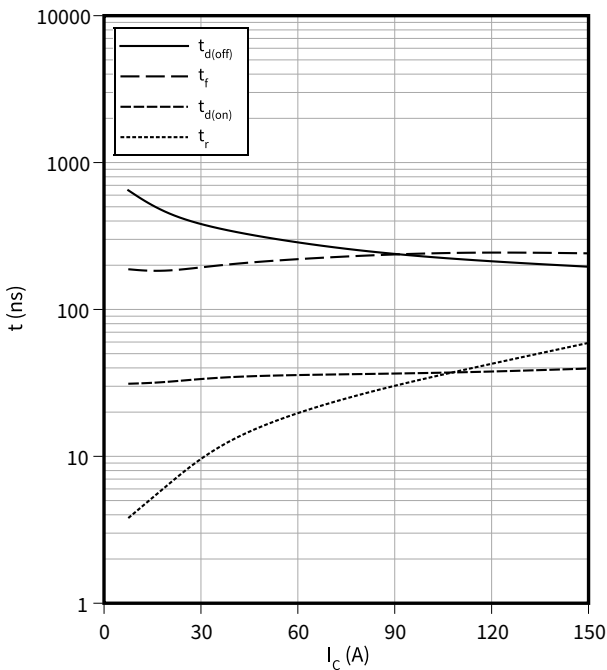
**Gate-emitter threshold voltage as a function of junction temperature**

$V_{GEth} = f(T_{vj})$   
 $I_c = 1.5 \text{ mA}$



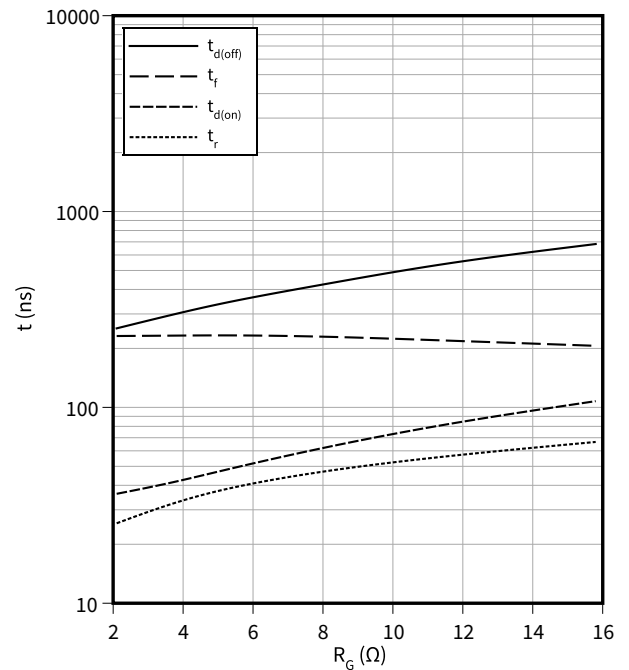
**Typical switching times as a function of collector current**

$t = f(I_c)$   
 $V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}, R_G = 2.1 \text{ } \Omega$



**Typical switching times as a function of gate resistor**

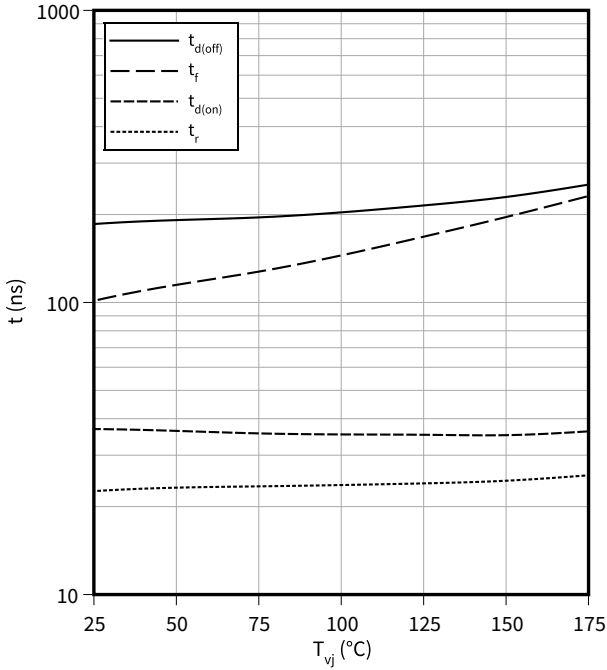
$t = f(R_G)$   
 $I_c = 75 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}$



**Typical switching times as a function of junction temperature**

$t = f(T_{vj})$

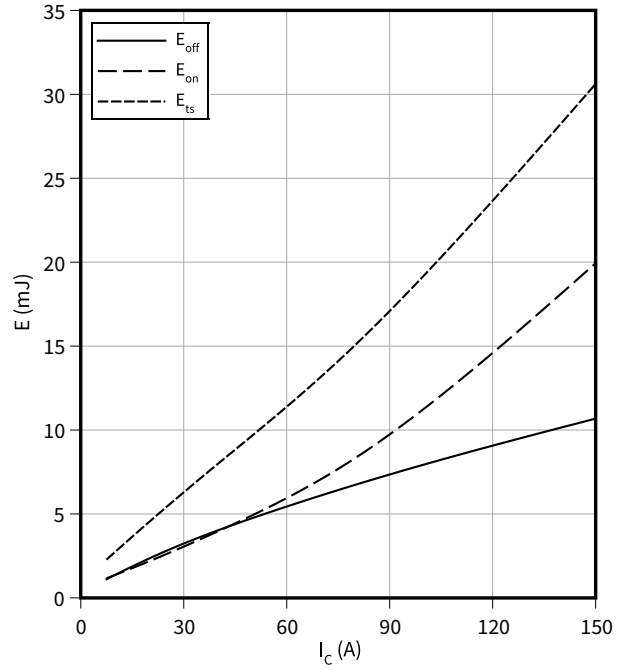
$I_C = 75 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 2.1 \Omega$



**Typical switching energy losses as a function of collector current**

$E = f(I_C)$

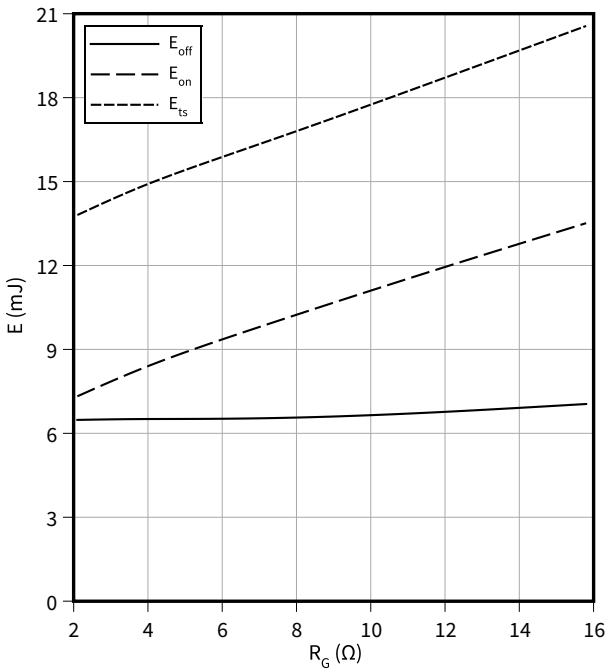
$V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}, R_G = 2.1 \Omega$



**Typical switching energy losses as a function of gate resistor**

$E = f(R_G)$

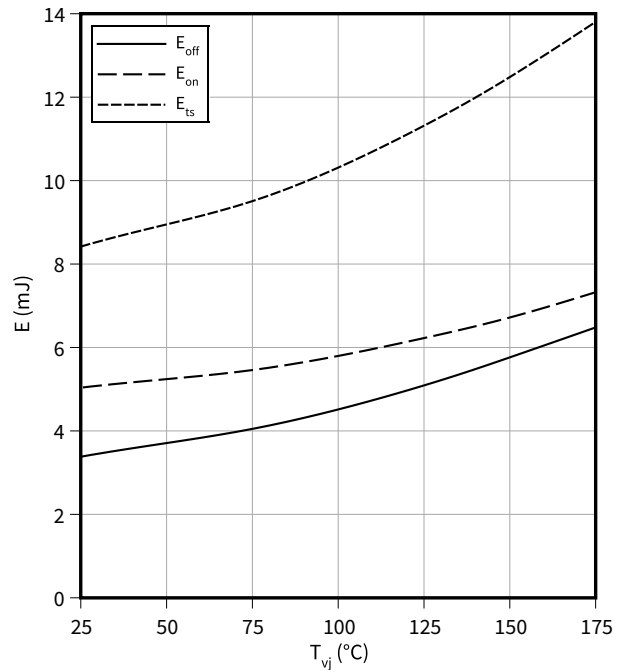
$I_C = 75 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}$



**Typical switching energy losses as a function of junction temperature**

$E = f(T_{vj})$

$I_C = 75 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 2.1 \Omega$

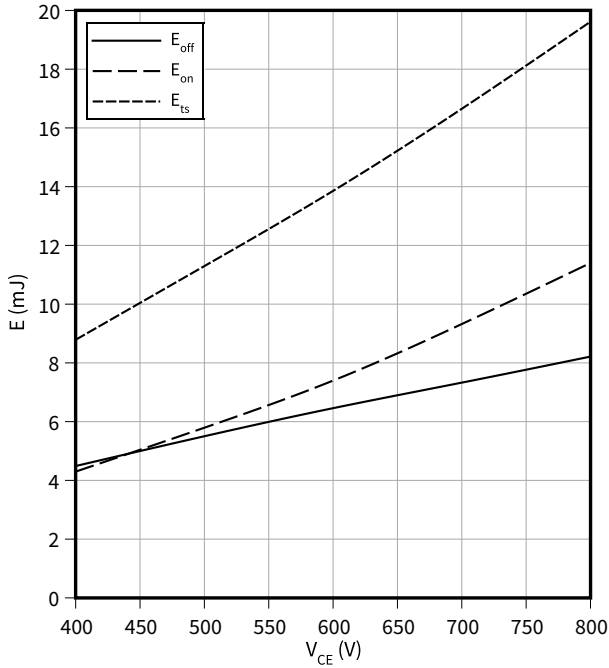


**3 Characteristics diagrams**

**Typical switching energy losses as a function of collector emitter voltage**

$E = f(V_{CE})$

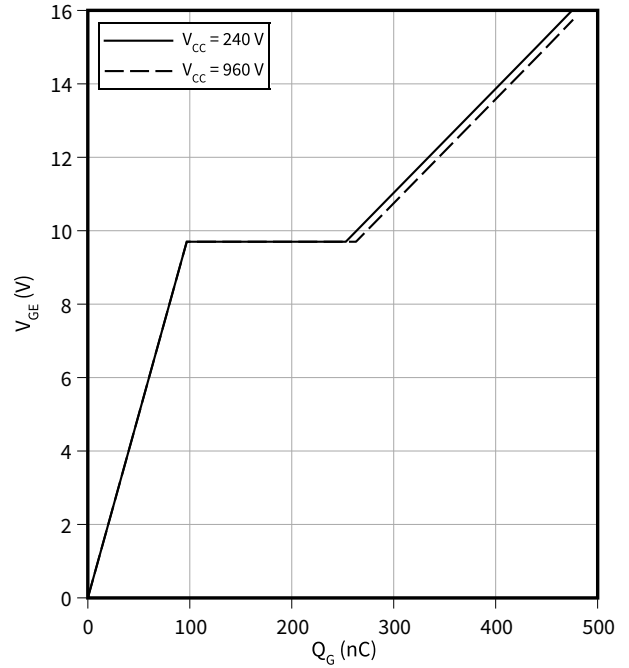
$I_C = 75 \text{ A}$ ,  $T_{vj} = 175 \text{ °C}$ ,  $V_{GE} = 0/15 \text{ V}$ ,  $R_G = 2.1 \text{ } \Omega$



**Typical gate charge**

$V_{GE} = f(Q_G)$

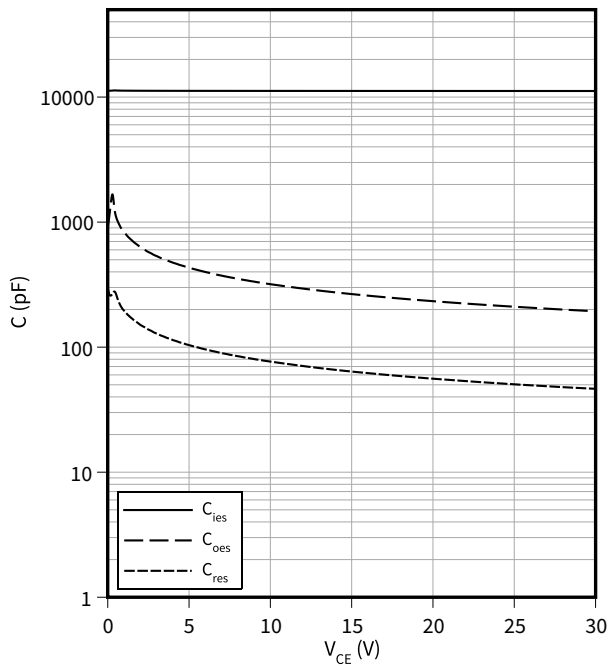
$I_C = 75 \text{ A}$



**Typical capacitance as a function of collector-emitter voltage**

$C = f(V_{CE})$

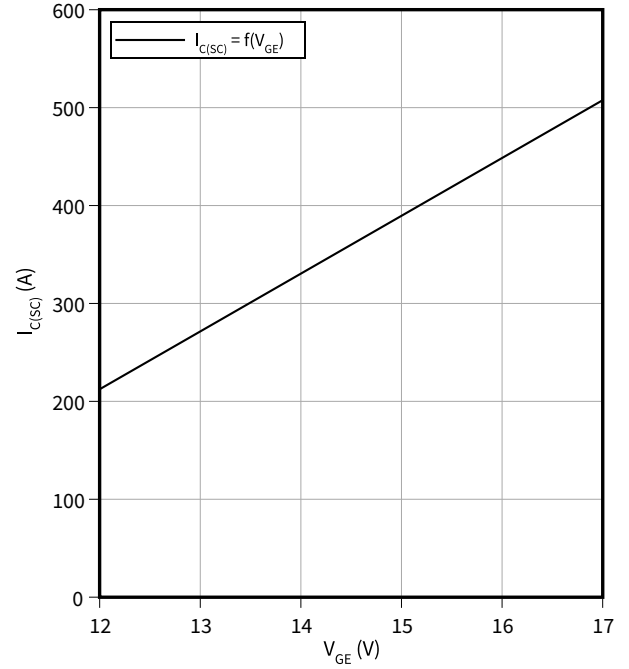
$f = 100 \text{ kHz}$ ,  $V_{GE} = 0 \text{ V}$



**Typical short circuit collector current as a function of gate-emitter voltage**

$I_{C(SC)} = f(V_{GE})$

$T_{vj} = 150 \text{ °C}$ ,  $V_{CC} \leq 600 \text{ V}$

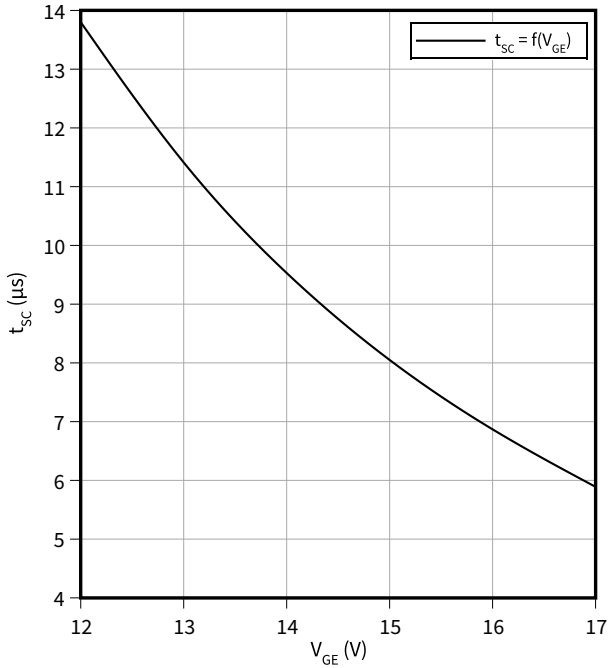


3 Characteristics diagrams

**Short circuit withstand time as a function of gate-emitter voltage**

$$t_{SC} = f(V_{GE})$$

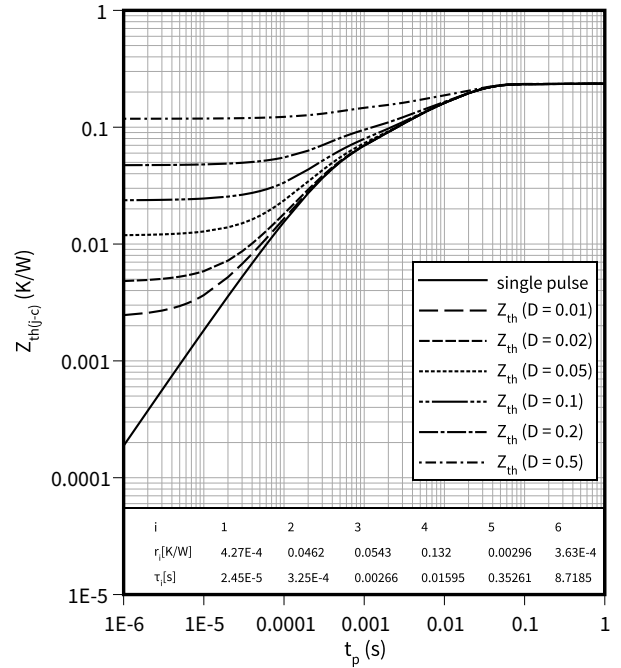
$T_{vj} \leq 150\text{ }^{\circ}\text{C}$ ,  $V_{CC} \leq 600\text{ V}$



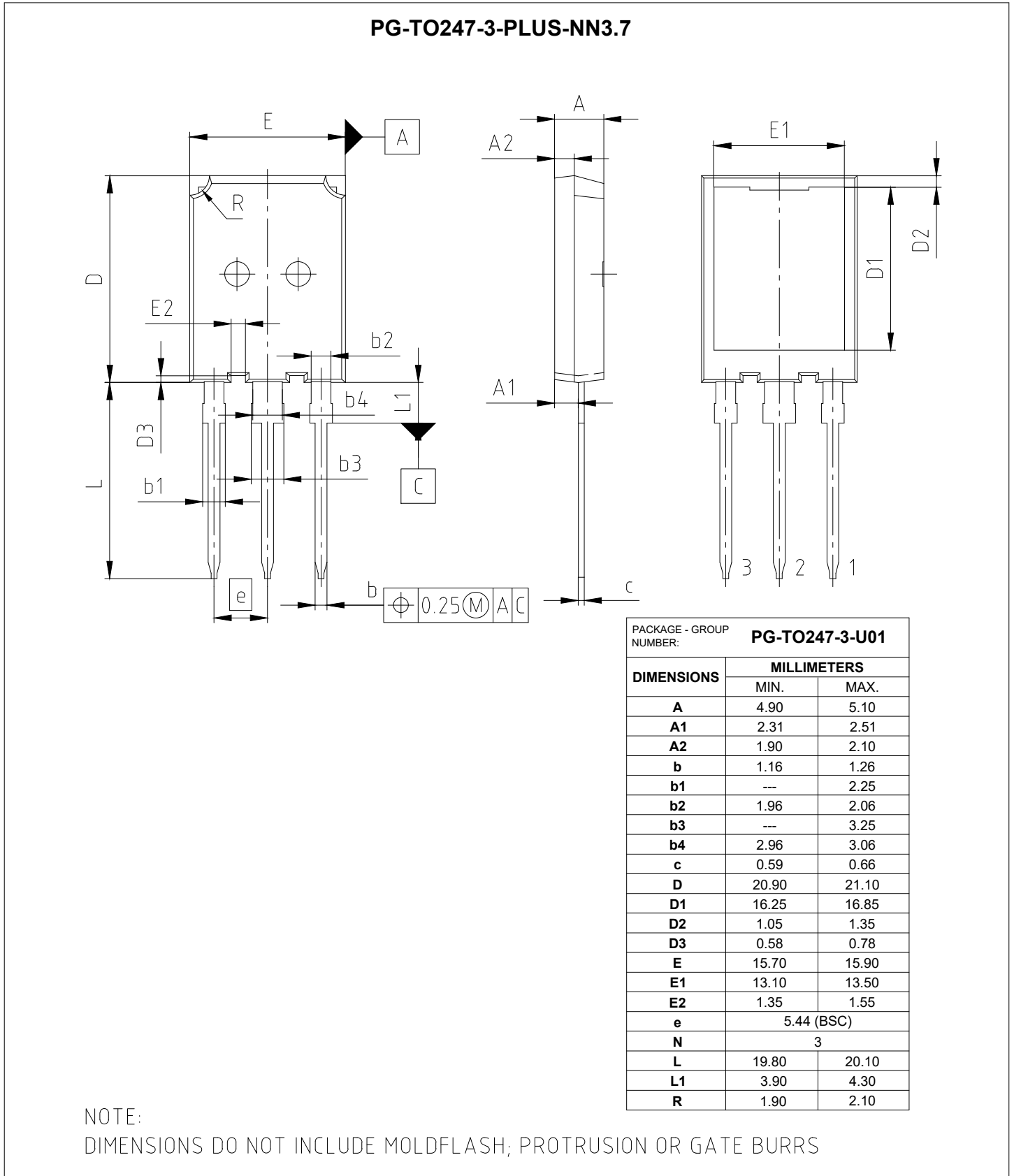
**IGBT transient thermal impedance as a function of pulse width**

$$Z_{th(j-c)} = f(t_p)$$

$$D = t_p/T$$

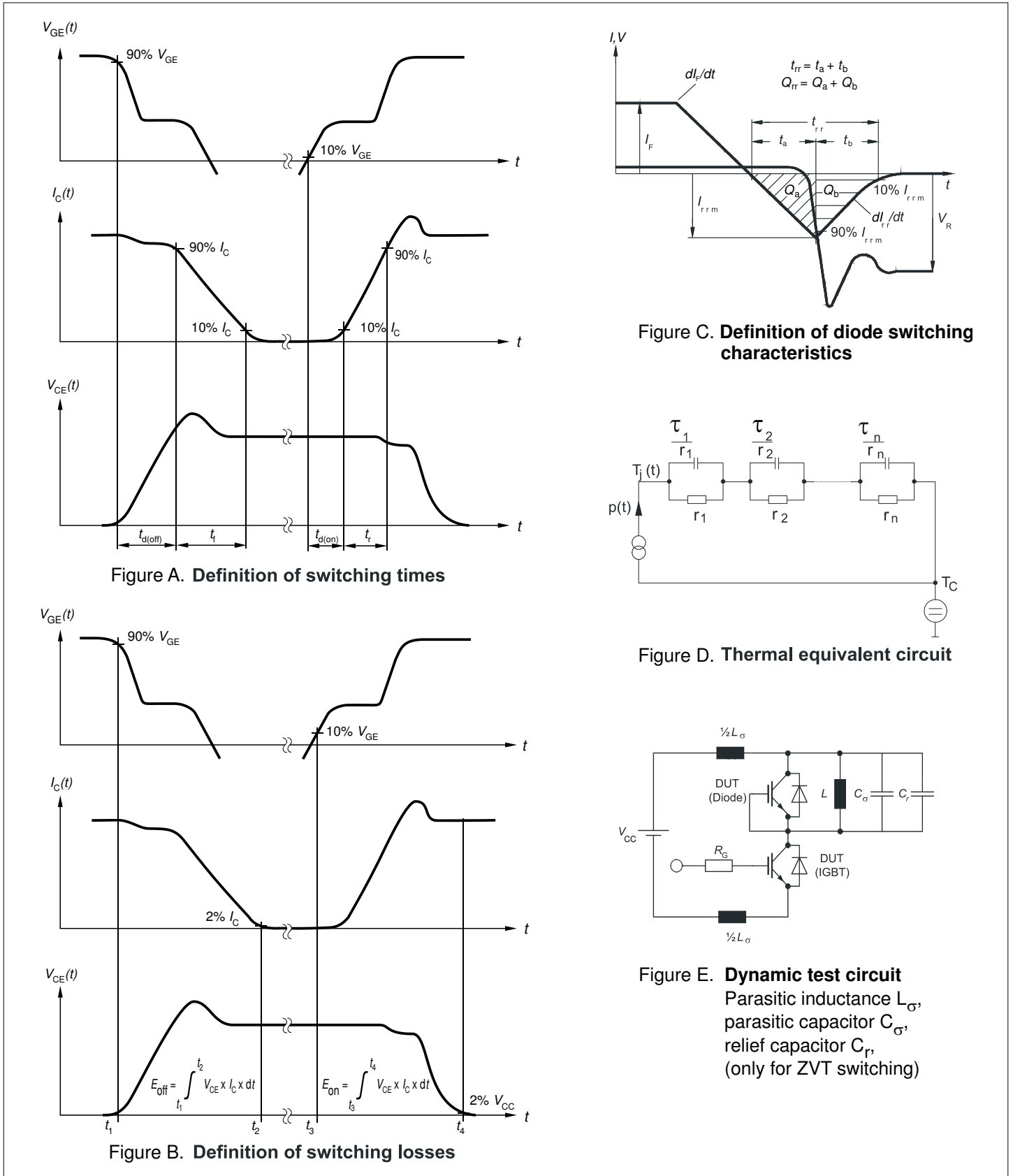


**4 Package outlines**



**Figure 1**

**5 Testing conditions**



**Figure 2**

## Revision history

Document revision	Date of release	Description of changes
0.10	2022-05-04	Target datasheet
1.00	2022-12-05	Final datasheet
1.10	2023-01-23	Correction of boundary condition of diagrams $I_{C(SC)} = f(V_{GE})$ and $t_{SC} = f(V_{GE})$ Change of product outline drawing on page 11

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**Document reference**

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